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## FDA18N50 N-Channel UniFET<sup>™</sup> MOSFET 500 V, 19 A, 265 mΩ

#### Features

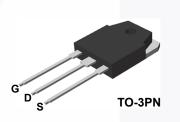
- $R_{DS(on)}$  = 265 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C<sub>rss</sub> (Typ. 25 pF)
- 100% Avalanche Tested

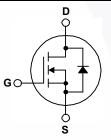
#### Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDA18N50	Unit
V <sub>DSS</sub>	Drain-Source Voltag	ge		500	V
I <sub>D</sub>	Drain Current	- Continuous ( $T_C = 25^{\circ}C$ ) - Continuous ( $T_C = 100^{\circ}C$ )		19 11.4	AA
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	76	A
V <sub>GSS</sub>	Gate-Source voltag	е		±30	V
E <sub>AS</sub>	Single Pulsed Avala	anche Energy	(Note 2)	945	mJ
I <sub>AR</sub>	Avalanche Current		(Note 1)	19	A
E <sub>AR</sub>	Repetitive Avalanch	ne Energy	(Note 1)	23	mJ
dv/dt	Peak Diode Recove	ery dv/dt	(Note 3)	4.5	V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate above 25°C		239 1.92	W W/°C
T <sub>J,</sub> T <sub>STG</sub>	Operating and Stora	age Temperature Range		-55 to +150	°C
TL	Maximum Lead Ter 1/8" from Case for	nperature for Soldering Purpose 5 Seconds	Э,	300	°C

### **Thermal Characteristics**

Symbol	Parameter	FDA18N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/W

FDA18N50 — N-Channel UniFET<sup>TM</sup> MOSFET

FDA18N50 — N-	N-Channel	In	nel	UniFl	E	E	M		MOS	FE	-					
<b>ity</b> ts	Unit		V	V/°C	μA	μΑ μΑ	nA	nA		V	Ω	S	pF	pF	pF	
nt	(										5		 )			

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

## **Electrical Characteristics** $T_{C} = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics	1		1	1	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$ , Referenced to $25^{\circ}C$		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$			1 10	μΑ μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-100	nA
On Charac	teristics			I		
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9.5A		0.220	0.265	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 9.5A	-	25		S
Dynamic C	Characteristics			r.		
C <sub>iss</sub>	Input Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V,		2200	2860	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0MHz	-	330	430	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250V, I <sub>D</sub> = 19A		55	120	ns
t <sub>r</sub>	Turn-On Rise Time	$R_{G} = 25\Omega$		165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	95	200	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	90	190	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 400V, I <sub>D</sub> = 19A		45	60	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10V		12.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)	-	19		nC
Drain-Sou	rce Diode Characteristics and Maximu	n Ratings		1	1	
I <sub>S</sub>	Maximum Continuous Drain-Source Dio	de Forward Current			19	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	orward Current			76	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 19A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 19A		500		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> /dt =100A/μs		5.4		μC

#### NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 4.7mH, I\_{AS} = 19A, V\_DD = 50V, R\_G = 25 $\Omega$ , Starting T\_J = 25°C

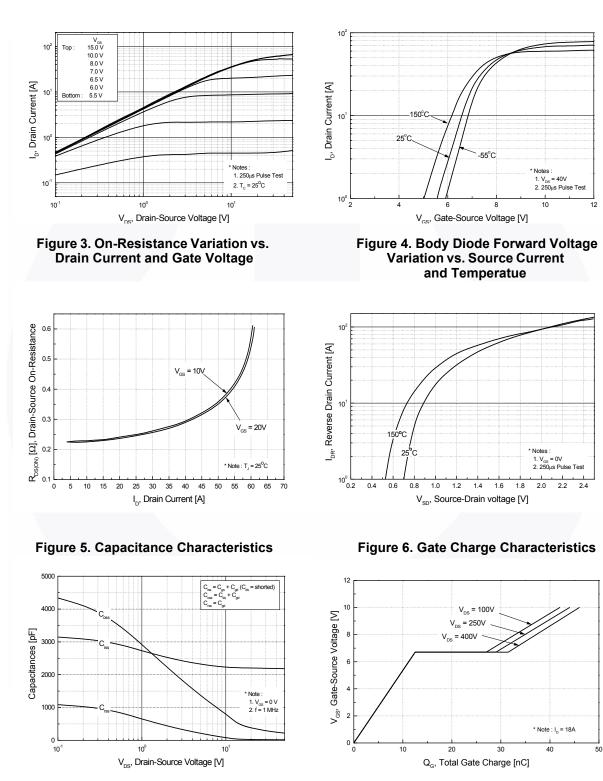
3. I\_{SD} \leq 19A, di/dt  $\leq$  200A/µs, V\_{DD}  $\leq$  BV\_{DSS}, Starting T\_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

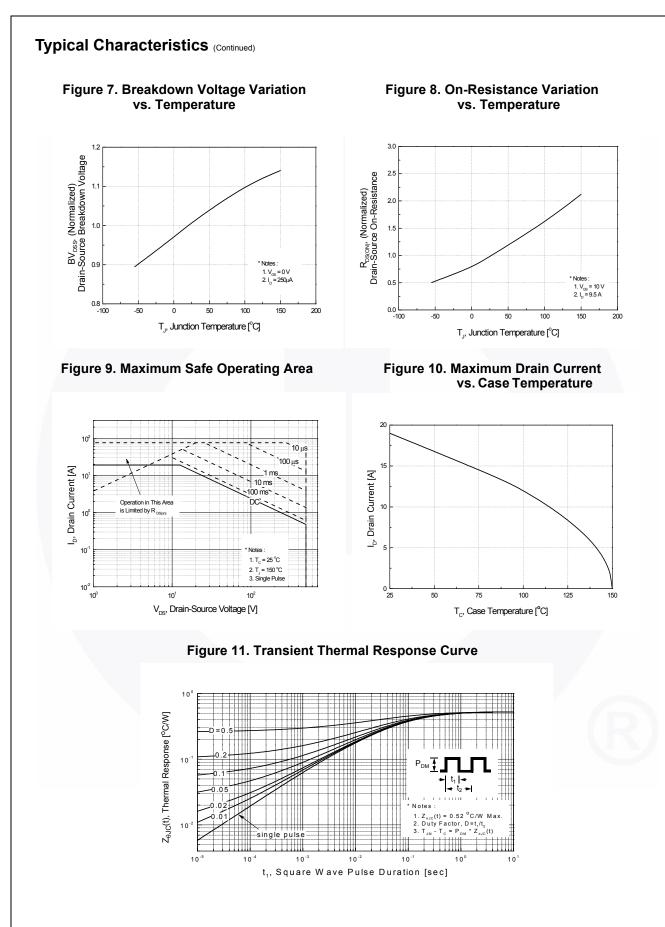
## **Typical Characteristics**



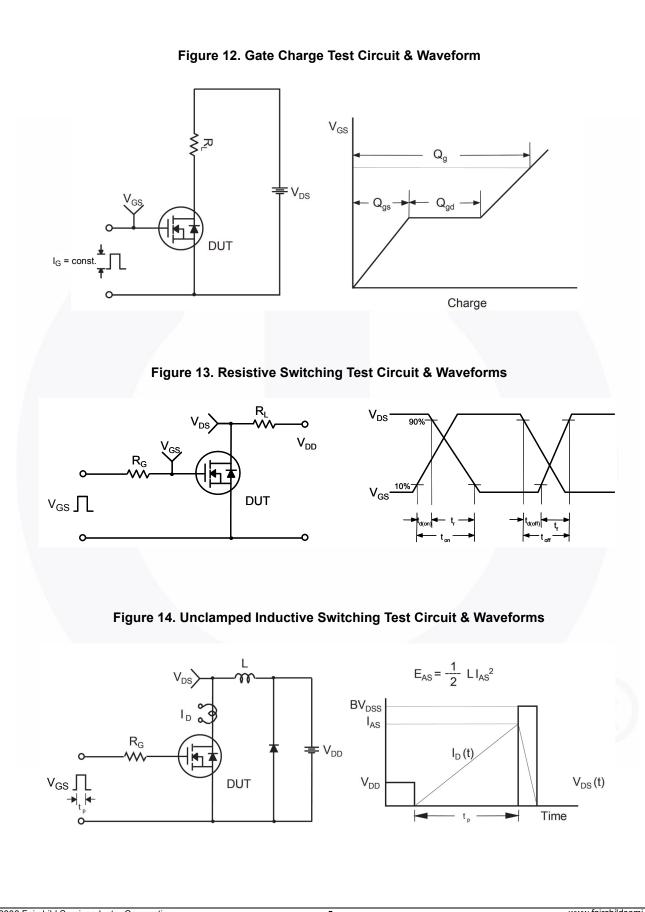
Figure 2. Transfer Characteristics



FDA18N50 — N-Channel UniFET<sup>TM</sup> MOSFET



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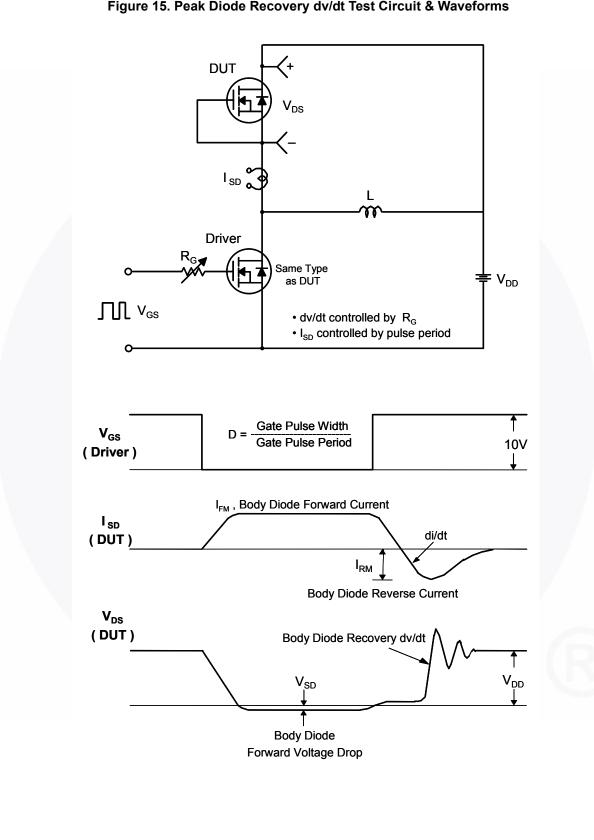
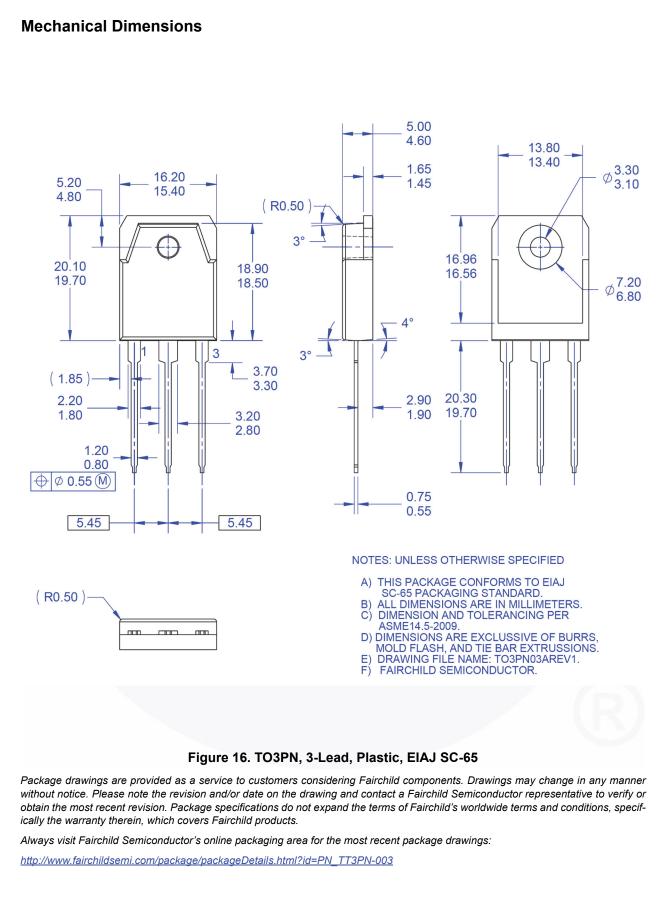


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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